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April 2016

# FAN7388 **ä5p**y**D£¶M**Ta**ÿ**‡QÀ

3 Half-Bridge Gate Driver

- Extended Allowable Negative V<sub>S</sub> Swing to -9.8 V for Signal Propagation at V<sub>BS</sub>=15 V
- Matched Propagation Delay Time Maximum: 50 ns
- 3.3 V and 5 V Input Logic Compatible
- Built-in Shoot-Through Prevention Circuit for All Channels with 270 ns Typical Dead Time
- Built-in Common Mode dv/dt Noise Canceling Circuit
- Built-in UVLO Functions for All Channels

# **Applications**

■ 3-Phase Motor Inverter Driver

#### **Related Resources**

- <u>AN-6076 Design and Application Guide of Bootstrap</u> <u>Circuit for High-Voltage Gate-Drive IC</u>
- AN-9052 Design Guide for Selection of Bootstrap Components
- <u>AN-8102 Recommendations to Avoid Short Pulse</u> Width Issues in HVIC Gate Driver Applications

#### Description

The FAN7388 is a monolithic three half-bridge gate-drive IC designed for high-voltage, high-speed driving MOS-FETs and IGBTs operating up to +600 V.

Fairchild's high-voltage process and common-mode noise canceling technique provide stable operation of high-side drivers under high-dv/dt noise circumstances.

An advanced level-shift circuit allows high-side gate driver operation up to  $V_S$ =-9.8 V (typical) for  $V_{BS}$ =15 V.

The UVLO circuits prevent malfunction when  $V_{DD}$  and  $V_{BS}$  are lower than the specified threshold voltage.

Output drivers typically source/sink 350 mA / 650 mA, respectively, which is suitable for three-phase half-bridge applications in motor drive systems.

**20-SOIC** 



# **Ordering Information**

Part Number	Package	Operating Temperature Range	Packing Method
FAN7388MX	20-SOIC	-40°C to +125°C	Tape & Reel

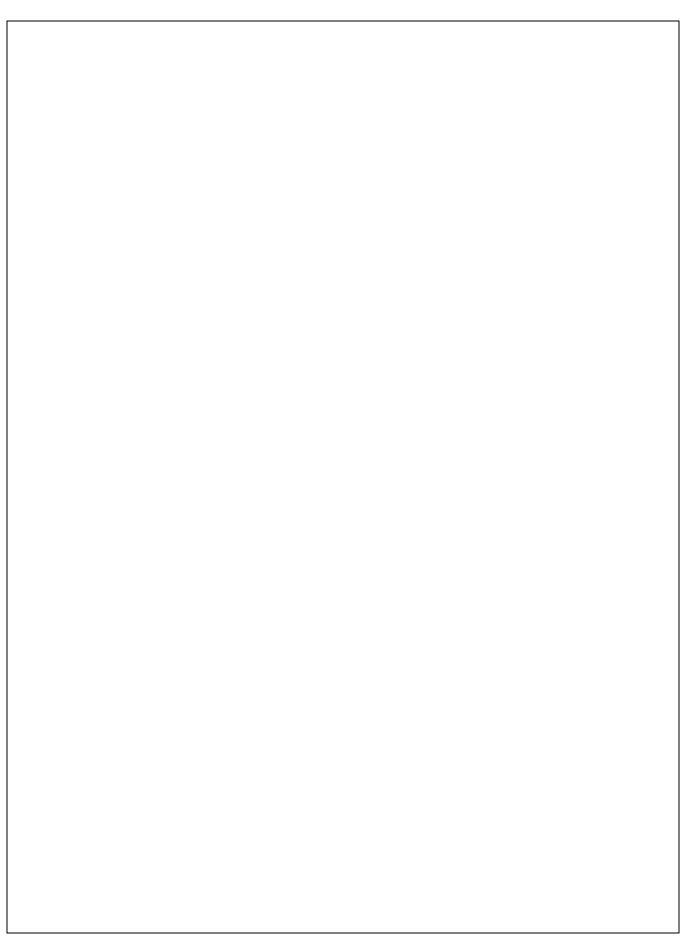




Figure 3. Pin Configuration (Top View)

# **Pin Definitions**

Pin#	Name	Description
1	HIN1	Logic input 1 for high-side gate 1 driver
2	LIN1	Logic input 1 for low-side gate 1 driver
3	HIN2	Logic input 2 for high-side gate 2 driver
4	LIN2	Logic input 2 for low-side gate 2 driver
5	HIN3	Logic input 3 for high-side gate 3 driver
6	LIN3	Logic input 3 for low-side gate 3 driver
7	LO3	Low-side gate driver 3 output
8	$V_{S3}$	High-side driver 3 floating supply offset voltage
9	HO3	High-side driver 3 gate driver output
10	$V_{B3}$	

# **Absolute Maximum Ratings**

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.  $T_A=25^{\circ}C$ , unless otherwise specified.

Symbol	Parameter	Min.	Max.	Unit
$V_{B}$	High-Side Floating Supply Voltage of $V_{B1,2,3}$	-0.3	625.0	V
$V_S$	High-Side Floating Supply Offset Voltage of $V_{S1,2,3}$	V <sub>B1,2,3</sub> -25	$V_{B1,2,3}$ +0.3	V
$V_{HO1,2,3}$	High-Side Floating Output Voltage	V <sub>S1,2,3</sub> -0.3	$V_{B1,2,3}$ +0.3	V
$V_{DD}$				

#### Notes:

- 1. Mounted on 76.2 x 114.3 x 1.6 mm PCB (FR-4 glass epoxy material).
- 2. Refer to the following standards:
  - JESD51-2: Integral circuits thermal test method environmental conditions natural convection
  - JESD51-3: Low effective thermal conductivity test board for leaded surface-mount packages.
- 3. Do not exceed P<sub>D</sub> under any circumstances.

# **Recommended Operating Conditions**

The Recommended Operating Conditions table defines the conditions for actual device operation. Recommended operating conditions are specified to ensure optimal performance to the datasheet specifications. Fairchild does not recommend exceeding them or designing to Absolute Maximum Ratings.

## **Electrical Characteristics**

 $V_{BIAS}$  ( $V_{DD}$ ,  $V_{BS1,2,3}$ )=15.0 V,  $T_A$ =25 C, unless otherwise specified. The  $V_{IN}$  and  $I_{IN}$  parameters are referenced to GND. The  $V_O$  and  $I_O$  parameters are referenced to GND and  $V_{S1,2,3}$  and are applicable to the respective outputs LO1,2,3 and HO1,2,3.

Symbol	Characteristics	Condition	Min.	Тур.	Max.	Unit
LOW-SIDE POWER SUPPLY SECTION						
$I_{QDD}$	Quiescent V <sub>DD</sub> Supply Current	V <sub>LIN1,2,3</sub> =0 V or 5 V		160	350	μΑ
I <sub>PDD1,2,3</sub>	Operating V <sub>DD</sub> Supply Current for each Channel	f <sub>LIN1,2,3</sub> =20 kHz, rms Value		500	900	μΑ
$V_{DDUV+}$	V <sub>DD</sub> Supply Under-Voltage Positive-Going Threshold	$V_{DD}$ =Sweep, $V_{BS}$ =15 V	7.2	8.2	9.0	V
$V_{DDUV}$	$V_{\mbox{\scriptsize DD}}$ Supply Under-Voltage Negative-Going Threshold	$V_{DD}$ =Sweep, $V_{BS}$ =15 V	6.8	7.8	8.5	V
V <sub>DDHYS</sub>	V <sub>DD</sub> Supply Under-Voltage Lockout Hysteresis	$V_{DD}$ =Sweep, $V_{BS}$ =15 V		0.4		V
BOOTSTR	APPED POWER SUPPLY SECTION					
I <sub>QBS1,2,3</sub>	Quiescent V <sub>BS</sub> Supply Current for each Channel	V <sub>HIN1,2,3</sub> =0 V or 5 V		50	120	μΑ
I <sub>PBS1,2,3</sub>	Operating V <sub>BS</sub> Supply Current for each Channel	f <sub>HIN1,2,3</sub> =20 kHz, rms Value		400	800	μΑ
V <sub>BSUV+</sub>	V <sub>BS</sub> Supply Under-Voltage Positive-going Threshold	V <sub>DD</sub> =15 V, V <sub>BS</sub> =Sweep	7.2	8.2	9.0	V
$V_{\rm BSUV}$	V <sub>BS</sub> Supply Under-Voltage Negative-going Threshold	V <sub>DD</sub> =15 V, V <sub>BS</sub> =Sweep	6.8	7.8	8.5	V
$V_{BSHYS}$	V <sub>BS</sub> Supply Under-Voltage Lockout Hysteresis	V <sub>DD</sub> =15 V, V <sub>BS</sub> =Sweep		0.4		V
$I_{LK}$	Offset Supply Leakage Current	V <sub>B1,2,3</sub> =V <sub>S1,2,3</sub> =600 V			10	μΑ
GATE DRI	VER OUTPUT SECTION					
$V_{OH}$	High-Level Output Voltage, $V_{BIAS}$ - $V_{O}$	I <sub>O</sub> =20 mA			1.0	V
$V_{OL}$	Low-Level Output Voltage, $V_O$	I <sub>O</sub> =20 mA			0.6	V
$I_{O+}$	Output HIGH Short-Circuit Pulsed Current <sup>(4)</sup>	$V_O$ =0 V, $V_{IN}$ =5 V with PW <10 $\mu$ s	250	350		mA
I <sub>O-</sub>	Output LOW Short-Circuit Pulsed Current <sup>(4)</sup>	V <sub>O</sub> I				

#### Note:

4. This parameter is guaranteed by design.

# **Dynamic Electrical Characteristics**

 $\mathsf{T_{A}=25~C,~V_{BIAS}~(V_{DD},~V_{BS1,2,3})=15.0~V,~V_{S1,2,3}=GND,~C_{Load}=1000~pF~unless~otherwise~specified.}$ 

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit	
$t_{ON}$	Turn-on Propagation Delay	V <sub>S1,2,3</sub> =0 V		130	220	ns	
$t_{OFF}$	Turn-off Propagation Delay	V <sub>S1,2,3</sub> =0 V		150	240	ns	
$t_{R}$	Turn-on Rise Time			50	120	ns	
$t_{F}$	Turn-off Fall Time			30	80	ns	
MT1	Turn-on Delay Matching I t <sub>ON(H)</sub> -t <sub>OFF(L)</sub> I				50	ns	
MT2	Turn-off Delay Matching I t <sub>OFF(H)</sub> -t <sub>ON(L)</sub> I				50	ns	
DT	Dead Time		100	270	440	ns	
MDT	Dead-time Matching I t <sub>DT1</sub> -t <sub>DT2</sub>						

# **Typical Characteristics**

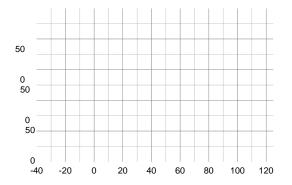


Figure 4. Turn-on Propagation Delay vs. Temp.

Figure 5. Turn-off Propagation Delay vs. Temp.

Figure 6. Turn-on Rise Time vs. Temp.

Figure 7. Turn-off Fall Time vs. Temp.

Figure 8. Turn-on Delay Matching vs. Temp.

Figure 9. Turn-off Delay Matching vs. Temp.

# Typical Characteristics (Continued)

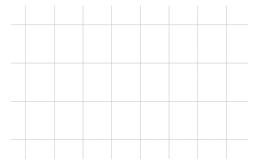


Figure 10. Dead Time vs. Temp.

Figure 11. Dead-Time Matching vs. Temp.

Figure 12. Quiescent  $V_{DD}$  Supply Current vs. Temp.

Figure 13. Quiescent  $V_{BS}$  Supply Current vs. Temp.

Figure 14. Operating  $V_{\mbox{\scriptsize DD}}$  Supply Current vs. Temp.

Figure 15. Operating  $\mathbf{V}_{\mathrm{BS}}$  Supply Current vs. Temp.

# Typical Characteristics (Continued)

Figure 18.  $V_{BS}$  UVLO+ vs. Temp.

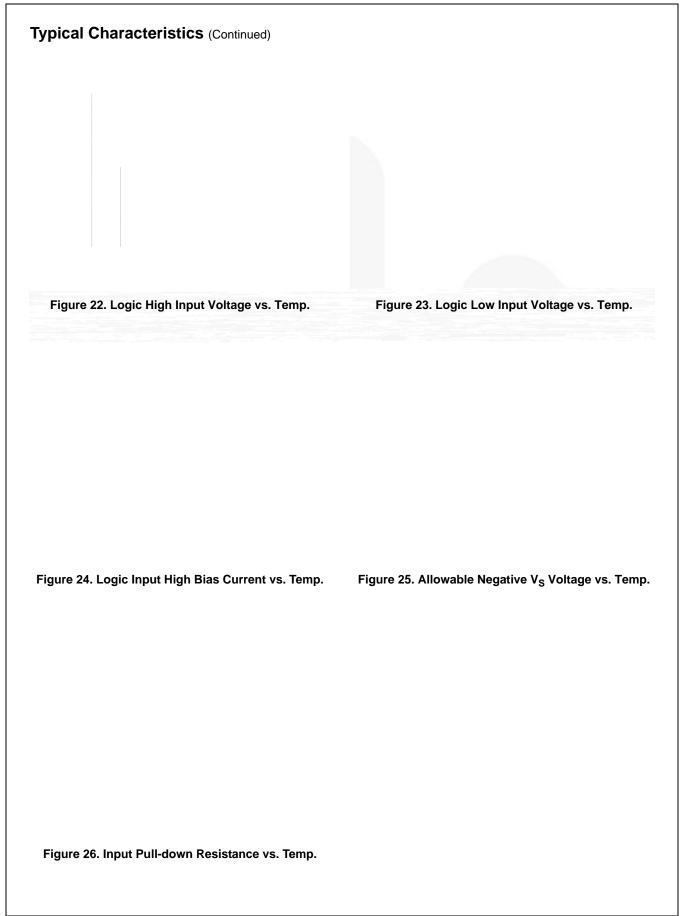
Figure 16. V<sub>DD</sub> UVLO+ vs. Temp.

Figure 19.  $V_{BS}$  UVLO- vs. Temp.

Figure 17.  $V_{DD}$  UVLO- vs. Temp.

Figure 20. High-Level Output Voltage vs. Temp.

Figure 21. Low-Level Output Voltage vs. Temp.



# **Application Information**

#### 1. Protection Function

## 1.1 Under-Voltage Lockout (UVLO)

The high- and low-side drivers include under-voltage lockout (UVLO) protection circuitry for each channel that monitors the supply voltage ( $V_{DD}$ ) and bootstrap capacitor voltage ( $V_{BS1,2,3}$ ) independently. It can be designed prevent malfunction when  $V_{DD}$  and  $V_{BS1,2,3}$  are lower than the specified threshold voltage. The UVLO hysteresis prevents chattering during power supply transitions.

#### 1.2 Shoot-Through Prevention Function

The FAN7388 has shoot-through prevention circuitry monitoring the high- and low-side control inputs. It can be designed to prevent outputs of high and low side from turning on at same time, as shown Figure 27 and 28.

#### 2. Operational Notes

The FAN7388 is a three half-bridge gate driver with internal, typical 270 ns dead-time for the three-phase brushless DC (BLDC) motor drive system, as shown in Figure 1.

Figure 29 shows a switching sequence of 120 electrical commutation for a three-phase BLDC motor drive system. The waveforms are idealized: they assumed that the generated back EMF waveforms are trapezoidal with flat

Figure 27. Waveforms for Shoot-Through Prevention

Figure 28. Waveforms for Shoot-Through Prevention

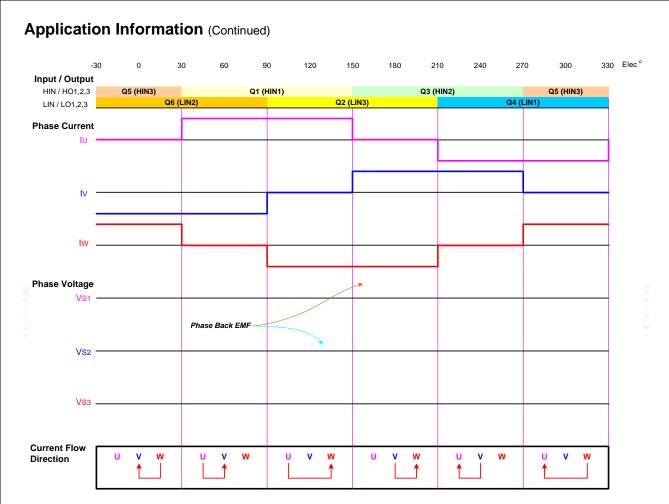


Figure 29. 120 Commutation Operation Waveforms for 3-Phase BLDC Motor Application

# **Switching Time Diagram**

Figure 30. Switching Time Definition

